

## TO-92 Plastic-Encapsulate Transistors

### KTA1266 TRANSISTOR (PNP)

#### FEATURES

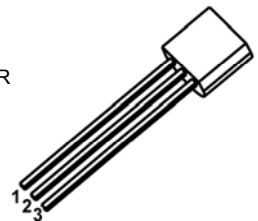
- Excellent  $h_{FE}$  Linearity
- Low Noise
- Complementary to KTC3198

#### MAXIMUM RATINGS ( $T_a=25\text{ }^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-0.15	A
$P_C$	Collector Power Dissipation	625	mW
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$

#### TO-92

1. EMITTER
2. COLLECTOR
3. BASE



#### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = -6\text{V}, I_C = -2\text{mA}$	70		400	
	$h_{FE(2)}$	$V_{CE} = -6\text{V}, I_C = -150\text{mA}$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-1.1	V
Transition frequency	$f_T$	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	80			MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			7	pF
Noise figure	NF	$V_{CE} = -6\text{V}, I_C = -0.1\text{mA}, f = 1\text{KHz}, R_g = 10\text{K}\Omega$			10	dB

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR
Range	70-140	120-240	200-400
Marking			